

N-Ch MOSFET

Features

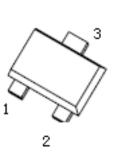
- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low R_{DS}(on)
- Operated at Low Logic Level Gate Drive

Product Summery

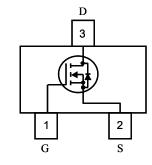
BVDSS	RDSON (TYP.)	ID (MAX)
20V	240mΩ	
20V	280mΩ	0.6A
20V	410mΩ	0.07
20V	450mΩ	

Applications

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift



SOT-723 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	± 8	V
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	400	mA
I _{DM}	Pulsed Drain Current ²	1.2	А
P _D @T _A =25℃	Total Power Dissipation ³	0.150	W
R _{θJA}	Thermal Resistance from Junction to Ambient (note 1)	823	°C/W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
TL	Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	260	°C



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Electrical Characteristics (T_J=25⁻¹C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V	
$\triangle BV_{DSS} / \triangle T_J$	BV _{DSS} Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=1mA		0.05		V/℃	
	Static Drain-Source On-Resistance	V _{GS} =4.5V , I _D =0.4A	240 4		450		
R _{DS(ON)}		V _{GS} =2.5V , I _D =0.3A		280	765	765 ^m Ω	
· (D3(ON)		V _{GS} =1.8V , I _D =0.2A		410	850		
		V _{GS} =1.5V , I _D =0.1A		450	950	mΩ	
V _{GS(th)}	Gate Threshold Voltage		0.35		1.0	V	
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	−V _{GS} =V _{DS} , I _D =250uA		-3.7		mV/℃	
	Drain-Source Leakage Current	V _{DS} =16V , V _{GS} =0V , TJ=25℃			1	- uA	
I _{DSS}		V _{DS} =16V , V _{GS} =0V , T _J =55℃			5		
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V$, $V_{DS}=0V$			±10	uA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =0.1A		1.5		S	
T _{d(on)}	Turn-On Delay Time			5.8			
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		2.9			
T _{d(off)}	Turn-Off Delay Time	R _G =6Ω, I _D =0.1A		18		ns	
T _f	Fall Time			9			
C _{iss}	Input Capacitance			88			
C _{oss}	itput Capacitance V _{DS} =15V , V _{GS} =0V , f=1MHz			15		pF	
C _{rss}	Reverse Transfer Capacitance			10			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current ^{1,4}				100	mA
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			0.5	А
V _{SD}	Diode Forward Voltage ²	$V_{GS}\text{=}0V$, $I_{S}\text{=}0.2A$, $T_{J}\text{=}25^{\circ}\!\mathrm{C}$			1.2	V

Notes :

1, Surface mounted on FR4 board using the minimum recommended pad size.

2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.

3. Switching characteristics are independent of operating junction temperatures.

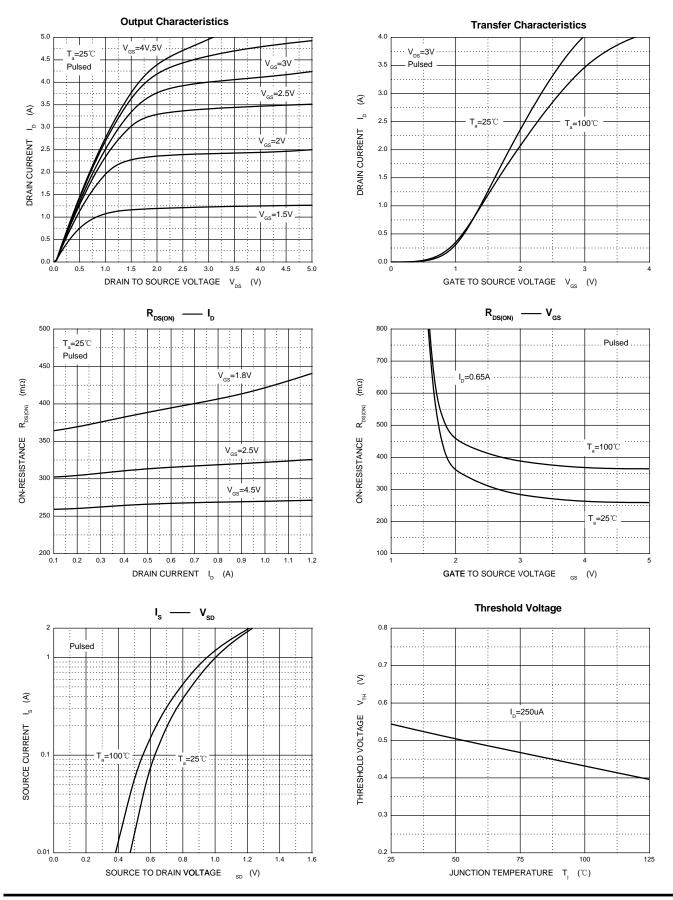
4. Guaranteed by design, not subject to producting.



WST2004

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Typical Performance Characteristics



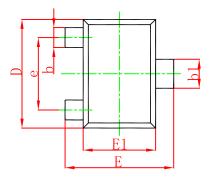
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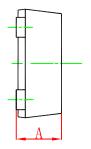


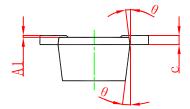
WST2004

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SOT-723 Package Outline Dimensions

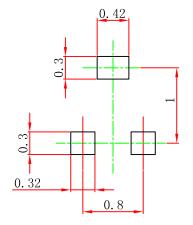






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.430	0.500	0.017	0.020	
A1	0.000	0.050	0.000	0.002	
b	0.170	0.270	0.007	0.011	
b1	0.270	0.370	0.011	0.015	
С	0.080	0.150	0.003	0.006	
D	1.150	1.250	0.045	0.049	
E	1.150	1.250	0.045	0.049	
E1	0.750	0.850	0.030	0.033	
е	0.800TYP.		0.031TYP.		
θ	7° REF.		7° REF.		

SOT-723 Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

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